

TOSHIBA Diode Silicon Epitaxial Pin Type

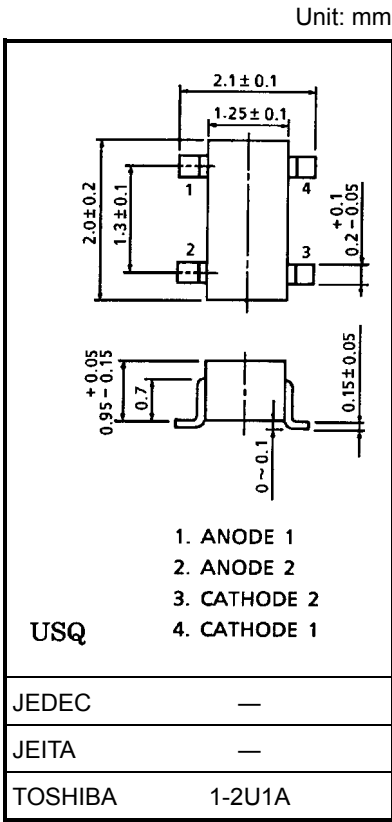
1SV312

VHF~UHF Band RF Attenuator Applications

- Two independent diodes mounted onto a 4-pin ultra compact package and it is suitable for high-density circuit design.
- Low capacitance: $C_T = 0.25 \text{ pF}$ (typ.)
- Low series resistance: $r_s = 3 \text{ } \Omega$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	50	V
Forward current	I_F	50	mA
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C



Weight: 0.006 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 10 \text{ } \mu\text{A}$	50	—	—	V
Reverse current	I_R	$V_R = 50 \text{ V}$	—	—	0.1	μA
Forward voltage	V_F	$I_F = 50 \text{ mA}$	—	0.95	1	V
Total capacitance	C_T	$V_R = 50 \text{ V}, f = 1 \text{ MHz}$	—	0.25	0.4	pF
Series resistance	r_s	$I_F = 10 \text{ mA}, f = 100 \text{ MHz}$	—	3	—	Ω

Marking

